

KSK123

SI N-CANNEL JUNCTION FET

T-29-25

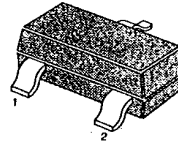
AF IMPEDANCE CONVERTER

- BUILT-IN DIODE BETWEEN G AND S
- LOW NV

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Drain Source Voltage	V _{DSO}	20	V
Drain Gate Voltage	V _{DGO}	20	V
Drain Source Current	I _{DSS}	2	mA
Drain Gate Current	I _{DGO}	2	mA
Gate Source Current	I _{GSS}	2	mA
Power Dissipation	P _D	200	mW
Operate Temperature	T _{OPR}	-20~80	°C
Storage Temperature	T _{STG}	-55~100	°C

SOT-23



1. Base 2. Emitter 3. Collector

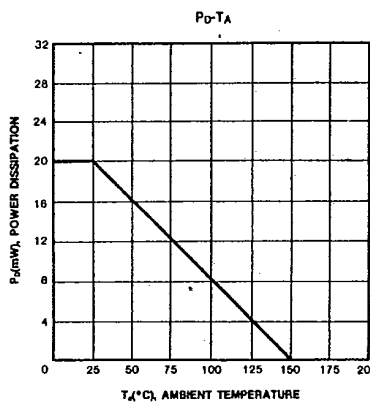
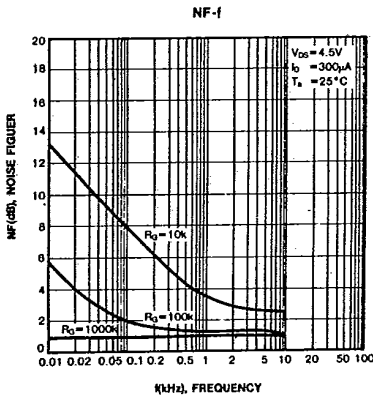
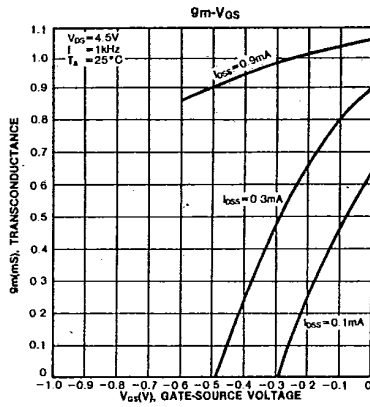
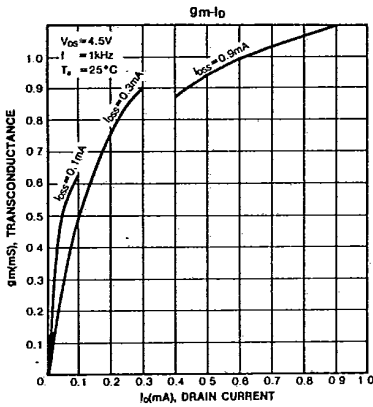
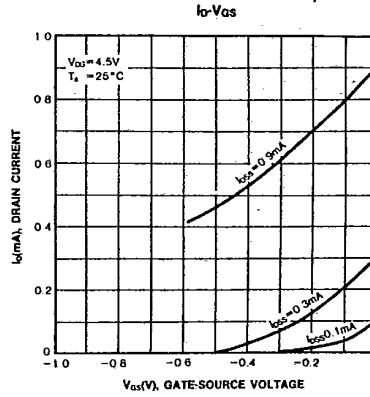
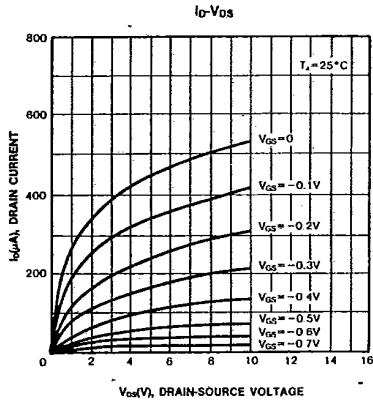
ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Drain Current	I _{DSS}	V _{DS} =4.5V, V _{GS} =0 R _S =2.2kohm ± 1%	130	200	470	μA
Transconductance	gm	V _{DS} =4.5V, V _{GS} =0 R _S =2.2kohm ± 1%, f=1kHz	0.9	1.6	4	mS μV
Voltage Gain	G _{V1}	C _G =10pF, A curve V _{DS} =4.5V, R _S =2.2kohm ± 1%	-1			dB
Voltage Gain	G _{V2}	C _G =10pF, E _G =10mV, f=70Hz V _{DS} =12V, R _S =2.2kohm ± 1%	0			dB
Voltage Gain	G _{V3}	C _G =10pF, E _G =10mV, f=70Hz V _{DS} =1.5V, R _S =2.2kohm ± 1%	-4			dB

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